TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRIAC

## TLP3051(S),TLP3052(S)

OFFICE MACHINE
HOUSEHOLD USE EQUIPMENT
TRIAC DRIVERSOLID STATE RELAY

The TOSHIBA TLP3051(S) and TLP3052(S) consists of a photo-triac optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP package.

• Peak Off-State Voltage : 600V(Min)

• Trigger LED Current : 15mA(Max)TLP3051

10mA(Max)TLP3052

On-State Current : 100mA(Max)Isolation Voltage : 5000Vrms(Min)

•UL Recognized :UL1577,File No.E67349

•SEMKO Approved :SS EN60065

SS EN60950, File No.9841102

•BSI Approved :BS EN60065, File No.8385

BS EN60950, File No.8386

Option(D4)type

VDE Approved :DIN VDE0884

Certificate No.68329

Maximum Operating Insulation Voltage  $:890V_{PK}$ Highest Permissible Over Voltage  $:8000 V_{PK}$ 

(Note)When a VDE0884 approved type is needed, please designate the "Option(D4)"

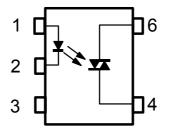
•Construction Mechanical Rating

	7.62 mm pich standard type	10.16 mm pich TLPXXXF type
Creepage Distance	7.0 mm (Min)	8.0 mm (Min)
Clearance	7.0 mm (Min)	8.0 mm (Min)
Insulation Thickness	0.5 mm (Min)	0.5 mm (Min)

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Weight: 0.39 g

## **PIN CONFIGURATION (TOP VIEW)**



- 1: ANODE
- 2: CATHODE
- 3: N.C.
- 4:TERMINAL1
- 6:TERMINAL2

## **MAXIMUM RATINGS(Ta=25°C)**

	CHARACTERISTIC		SYMBOL	RATING	UNIT	
LED	Forward Current	l <sub>F</sub>	50	mA		
	Forward Current Derating (Ta≥53°C)	ΔI <sub>F</sub> /°C	-0.7	mA /°C		
	Peak Forward Current (100µs pulse, 100pps)		I <sub>FP</sub>	1	Α	
H	Power Dissipation		P <sub>D</sub>	100	mW	
	Power Dissipation Derating (Ta≥25°C)		ΔP <sub>D</sub> /°C	-1.0	mW/°C	
	Reverse Voltage		V <sub>R</sub>	5	V	
	Junction Temperature		Tj	125	°C	
	Off-State Output Terminal Voltage	$V_{DRM}$	600	V		
	On-State RMS Current	Ta=25°C	I <sub>T(RMS)</sub>	100	mA	
	On-State NWO Guirent	Ta=70°C	T(RMS)	50		
ror	On-State Current Derating (Ta≥25°C)		ΔI <sub>T</sub> /°C	-1.1	mA /°C	
DETECTOR	Peak On-State Current (100µs pulse, 120pps)	I <sub>TP</sub>	2	Α		
DE	Peak Nonrepetitive Surge Current (Pw=10ms,DC=10	I <sub>TSM</sub>	1.2	Α		
	Power Dissipation	$P_D$	300	mW		
	Power Dissipation Derating (Ta≥25°C)	ΔP <sub>D</sub> /°C	-4.0	mW/°C		
	Junction Temperature	Tj	115	°C		
Ope	rating Temperature Range		T <sub>opr</sub>	-40~100	°C	
Stor	age Temperature Range	T <sub>stg</sub>	-55~150	°C		
Lea	d Soldering Temperature (10s)	T <sub>sol</sub>	260	°C		
Tota	al Package Power Dissipation	P <sub>T</sub>	330	mW		
Tota	al Package Power Dissipation Derating (Ta≥25°C)	ΔP <sub>T</sub> /°C	-4.4	mW /°C		
Isola	ation Voltage (AC,1min. , R.H.≤60%)	BVS	5000	Vrms		

(Note 2)Device considered a two terminal device :Pins1,2 and 3 shorted together and pin4 and pin6 shorted together.

### **RECOMMENDED OPERATING CONDITIONS**

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	$V_{AC}$	_	_	240	V <sub>ac</sub>
Forward Current	I <sub>F</sub> *	15	20	25	mA
Peak On-State Current	I <sub>TP</sub>	_	_	1	Α
Operating Temperature	$T_{opr}$	-25	_	85	°C

<sup>\*</sup>In The case of TLP3052

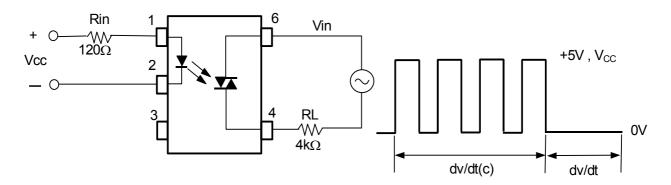
## INDIVIDUAL ELECTRICAL CHARACTERISTICS(Ta=25°C)

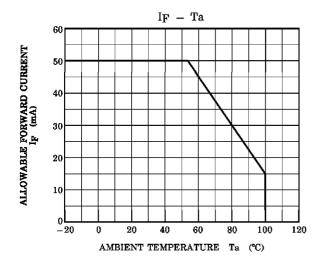
	CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
	Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 10 mA	1.0	1.15	1.3	V
ED	Reverse Current	I <sub>R</sub>	V <sub>R</sub> = 5 V	_	_	10	μΑ
	Capacitance	Ст	V = 0, f=1MHz	_	30	_	pF
2	Peak Off-State Current	I <sub>DRM</sub>	V <sub>DRM</sub> =600V	_	10	1000	nA
0 1	Peak On-State Voltage	$V_{TM}$	I <sub>TM</sub> =100mA	_	1.7	3.0	V
S	Holding Current	I <sub>H</sub>	_	_	1.0	_	mA
T	Critical Rate of Rise of Off-State Voltage	dv/dt	Vin=240Vrms , Ta=85°C (Note3		500	_	V/µs
D E	Critical Rate of Rise of Commutating Voltage	dv/dt(c)	Vin=60Vrms , IT=15mA (Note3	_	0.2	_	V/µs

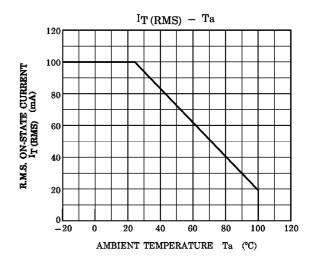
**COUPLED ELECTRICAL CHARACTERISTICS(Ta=25°C)** 

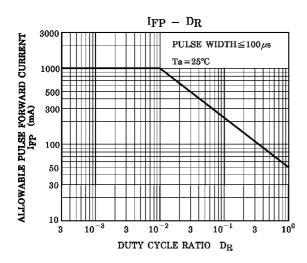
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Trigger LED Current	TLP3051	l	V <sub>T</sub> =6V	_	_	15	- mA	
Trigger LED Current	TLP3052	- I <sub>FT</sub>	V <sub>1</sub> -0V	_	5	10		
Capacitance (Input to Ou	tput)	Cs	VS=0 , f=1MHz	_	0.8		- pF	
Isolation Resistance		Rs	VS=500V(R.H.≤60%)	5×10 <sup>10</sup>	10 <sup>14</sup>	_	Ω	
Isolation Voltage		BVs	AC , 1minute	5000	_	_	Vrms	
			AC , 1second,in oil	_	10000	_		
			DC , 1minute,in oil		10000		Vdc	

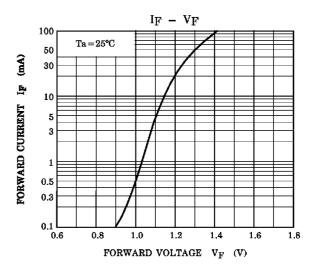
## (Note 3)dv/dt TEST CIRCUIT

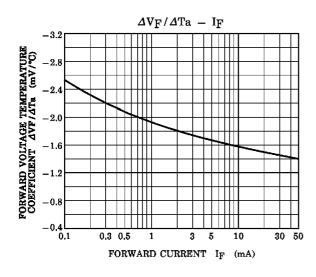


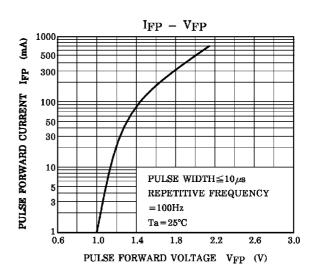


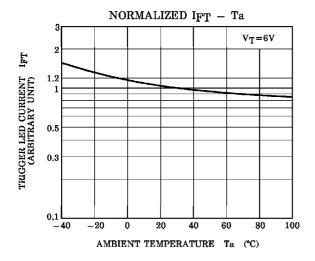


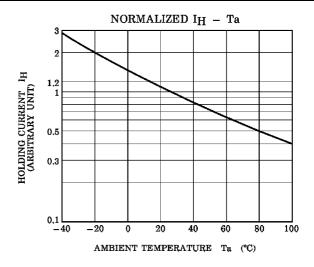


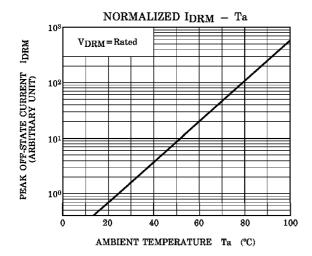


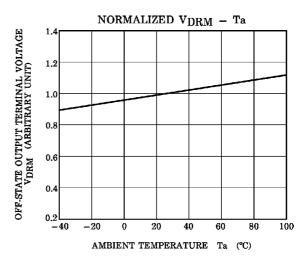


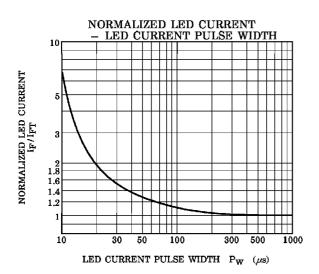












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